

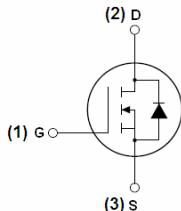


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MAITUO ELECTRONIC

## MT3018 AS N-Channel Enhancement Mode Power MOSFET

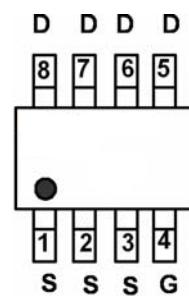
### Description

The MT3018AS uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.



### General Features

- $V_{DS} = 30V, I_D = 18A$
- $R_{DS(ON)} < 7m\Omega @ V_{GS}=10V$
- $R_{DS(ON)} < 10m\Omega @ V_{GS}=4.5V$
- High density cell design for ultra low Rdson
- Fully characterized Avalanche voltage and current



### Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

**SOP-8**

**Marking** :3018AS

### Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	18	A
Drain Current-Continuous( $T_A=100^\circ C$ )	$I_D (100^\circ C)$	12.7	A
Pulsed Drain Current	$I_{DM}$	48	A
Maximum Power Dissipation	$P_D$	3	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ C$

### Thermal Characteristic

Thermal Resistance, Junction-to-Ambient <sup>(Note 2)</sup>	$R_{\theta JA}$	42	$^\circ C/W$
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### Electrical Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	30	33	-	V
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{DS}}=30\text{V}, V_{\text{GS}}=0\text{V}$	-	-	1	$\mu\text{A}$
Gate-Body Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}=\pm20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	$\pm100$	nA
<b>On Characteristics</b> <sup>(Note 3)</sup>						
Gate Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	0.9	1.1	1.4	V
Drain-Source On-State Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=12\text{A}$	-	5.5	7	$\text{m}\Omega$
		$V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=10\text{A}$	-	6.5	10	
Forward Transconductance	$g_{\text{FS}}$	$V_{\text{DS}}=5\text{V}, I_{\text{D}}=12\text{A}$	5	-	-	S
<b>Dynamic Characteristics</b> <sup>(Note 4)</sup>						
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=15\text{V}, V_{\text{GS}}=0\text{V}, F=1.0\text{MHz}$	-	2100	-	PF
Output Capacitance	$C_{\text{oss}}$		-	460	-	PF
Reverse Transfer Capacitance	$C_{\text{rss}}$		-	230	-	PF
<b>Switching Characteristics</b> <sup>(Note 4)</sup>						
Turn-on Delay Time	$t_{\text{d(on)}}$	$V_{\text{DD}}=10\text{V}, I_{\text{D}}=12\text{A}$ $V_{\text{GS}}=10\text{V}, R_{\text{GEN}}=2.7\Omega$	-	20	-	nS
Turn-on Rise Time	$t_{\text{r}}$		-	15	-	nS
Turn-Off Delay Time	$t_{\text{d(off)}}$		-	60	-	nS
Turn-Off Fall Time	$t_{\text{f}}$		-	10	-	nS
Total Gate Charge	$Q_{\text{g}}$	$V_{\text{DS}}=15\text{V}, I_{\text{D}}=12\text{A}, V_{\text{GS}}=10\text{V}$	-	41	-	nC
Gate-Source Charge	$Q_{\text{gs}}$		-	14	-	nC
Gate-Drain Charge	$Q_{\text{gd}}$		-	11	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage <sup>(Note 3)</sup>	$V_{\text{SD}}$	$V_{\text{GS}}=0\text{V}, I_{\text{s}}=18\text{A}$	-	-	1.2	V
Diode Forward Current <sup>(Note 2)</sup>	$I_{\text{s}}$		-	-	18	A

#### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production



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### Typical Electrical and Thermal Characteristics (Curves)

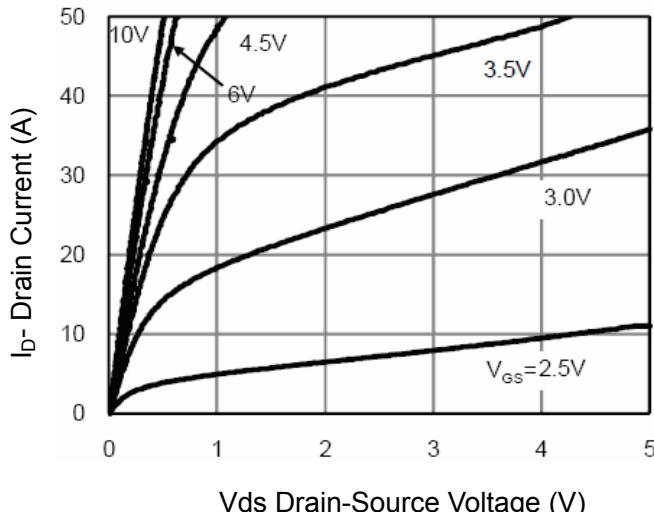


Figure 1 Output Characteristics

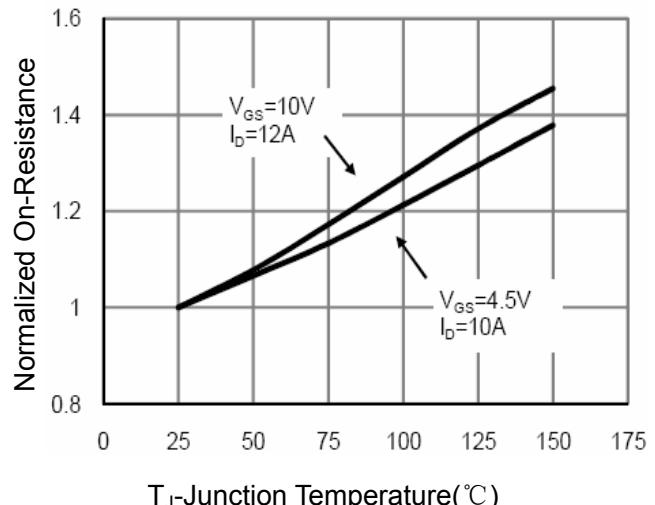


Figure 4  $R_{dson}$ -Junction Temperature

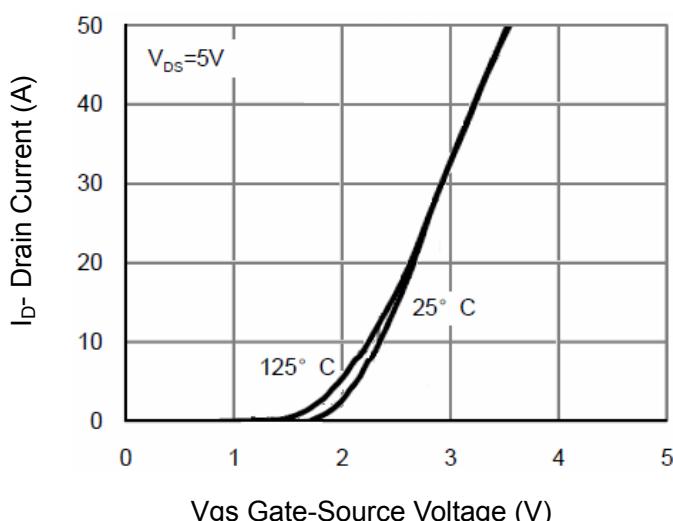


Figure 2 Transfer Characteristics

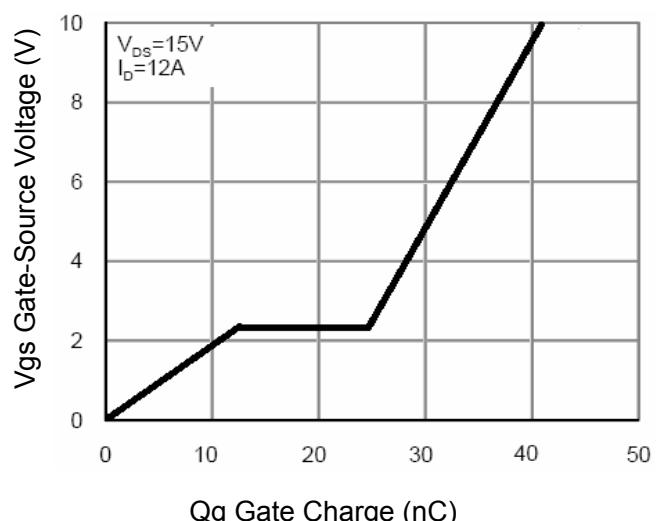


Figure 5 Gate Charge

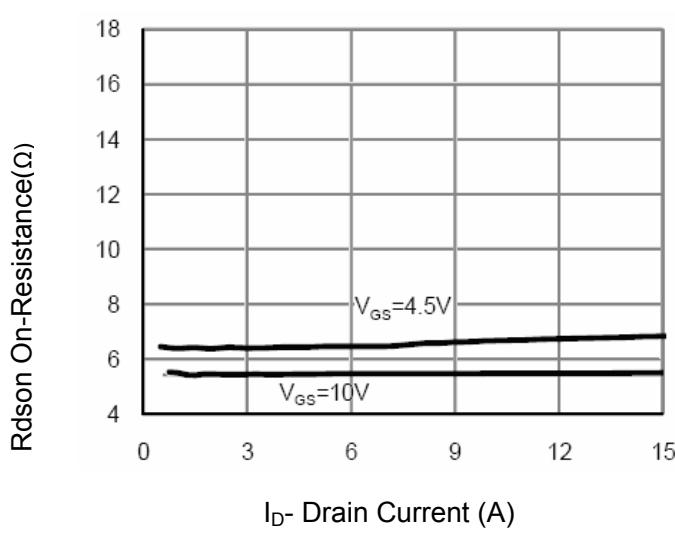


Figure 3  $R_{dson}$ - Drain Current

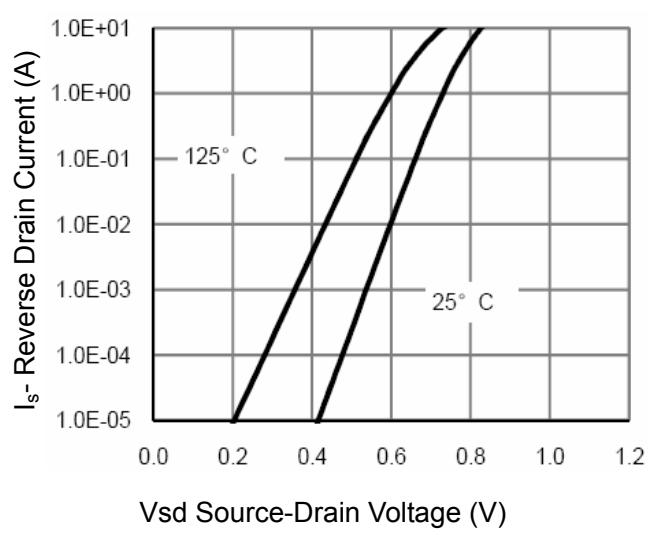
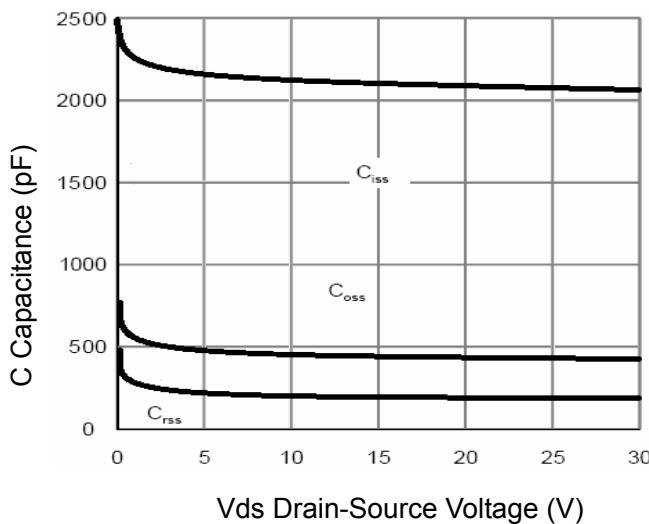


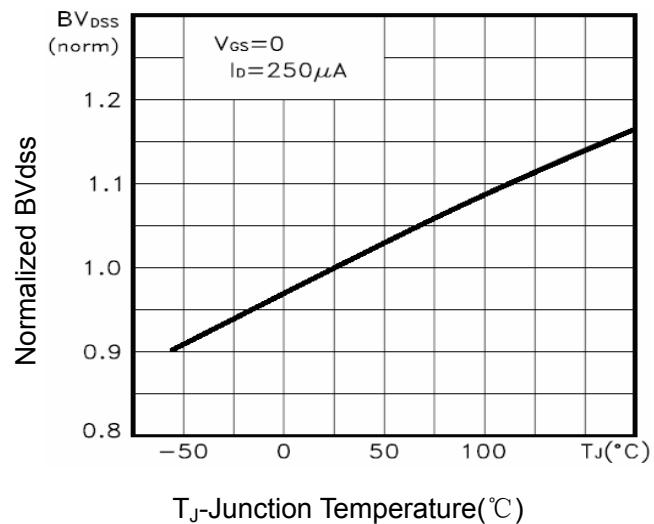
Figure 6 Source-Drain Diode Forward



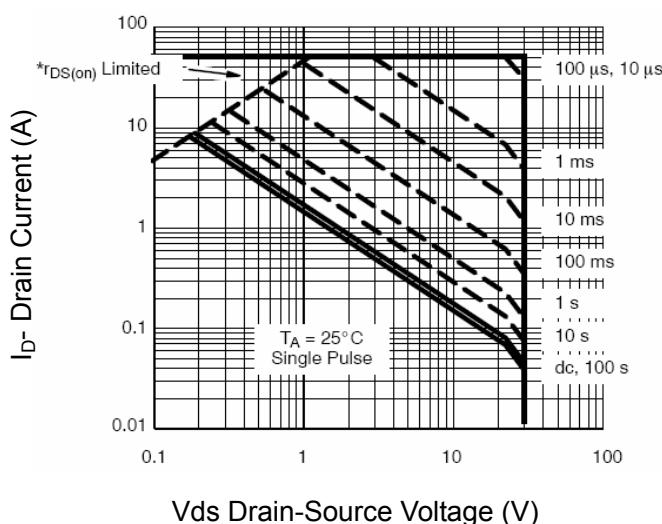
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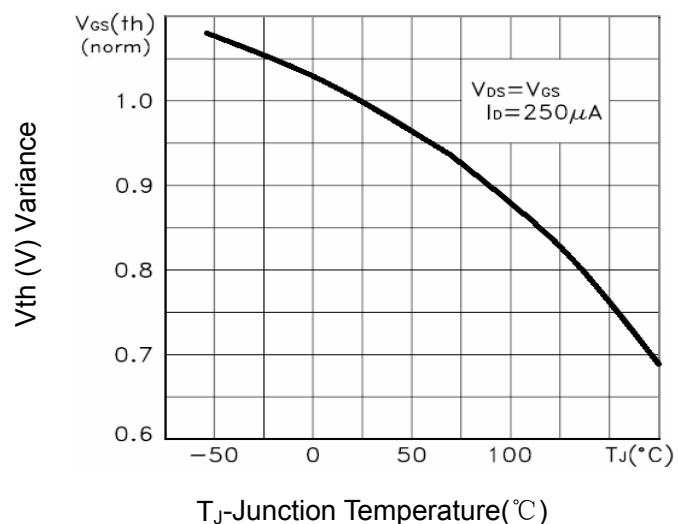
**Figure 7 Capacitance vs Vds**



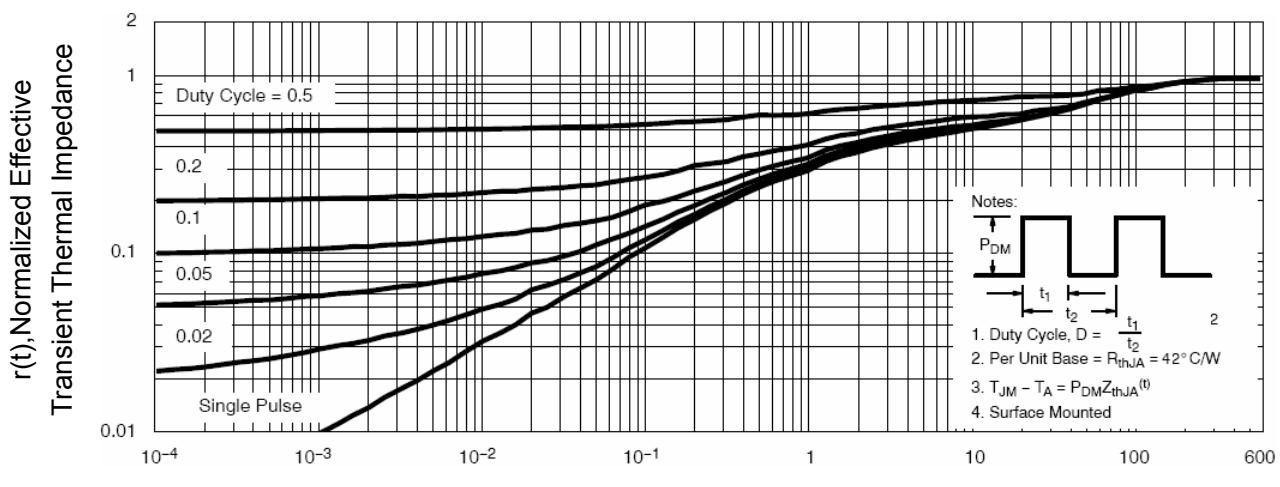
**Figure 9  $BV_{DSS}$  vs Junction Temperature**



**Figure 8 Safe Operation Area**



**Figure 10  $V_{GS(th)}$  vs Junction Temperature**

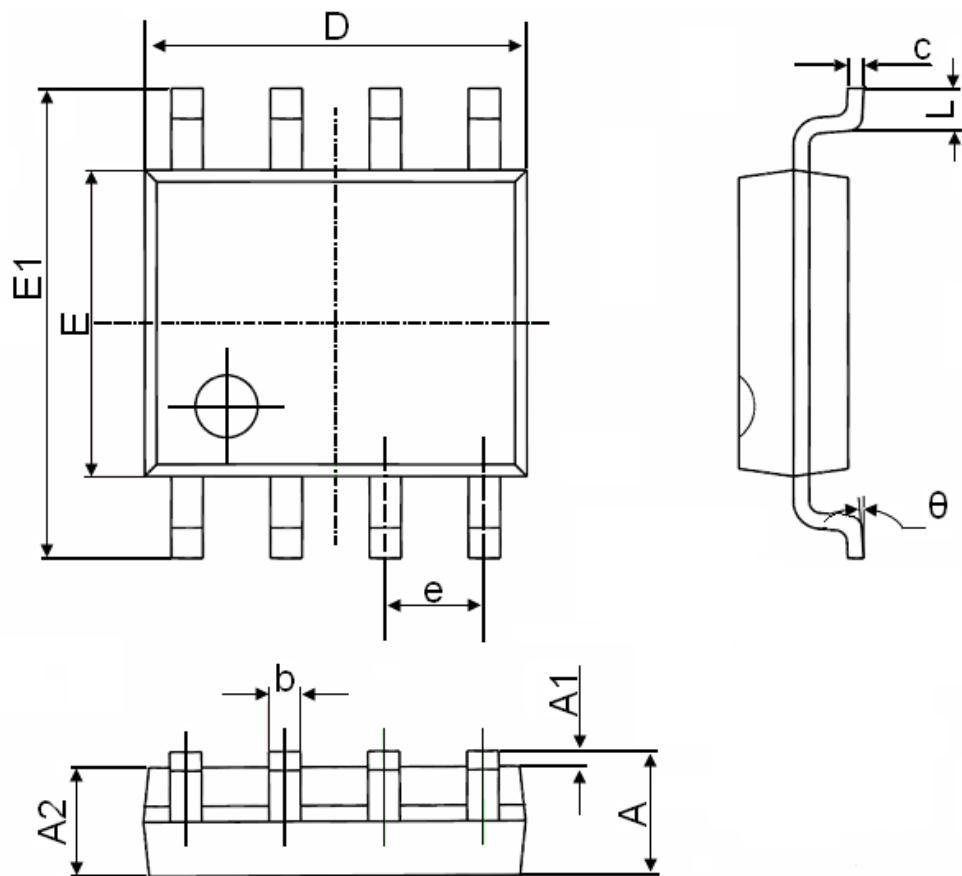


**Figure 11 Normalized Maximum Transient Thermal Impedance**



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### SOP-8 Package Information



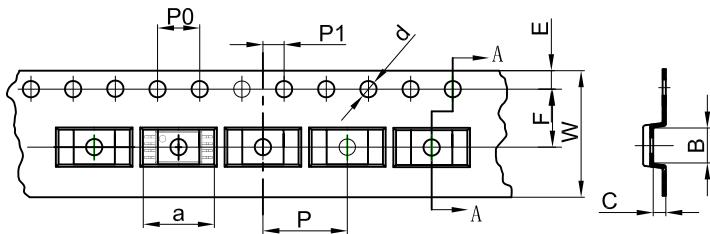
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



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## SOP8 Tape and Reel

### SOP8 Embossed Carrier Tape



#### Packaging Description:

SOP8 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3,000 units per 13" or 33cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

ALL DIM IN mm

Dimensions are in millimeter										
Pkg type	a	B	C	d	E	F	P0	P	P1	W
SOP8	6.40	5.40	2.10	$\varnothing 1.50$	1.75	5.50	4.00	8.00	2.00	12.00

### SOP8 Tape Leader and Trailer

